

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D $T_A = +25^\circ\text{C}$
20V	0.17 Ω @ $V_{GS} = 4.5\text{V}$	1.35A
	0.23 Ω @ $V_{GS} = 2.5\text{V}$	1.15A
	0.25 Ω @ $V_{GS} = 1.8\text{V}$	1.10A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features

- Low On-Resistance
- Very Low Gate Threshold Voltage $V_{GS(TH)}$, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

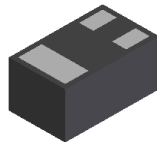
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 ⁽⁶⁴⁾
- Weight: 0.001 grams (approximate)

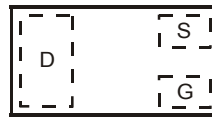
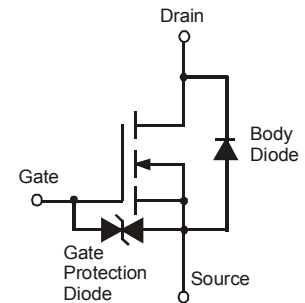


ESD PROTECTED

X1-DFN1006-3



Bottom View


 Top View
Internal Schematic


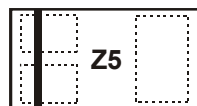
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2250UFB-7B	X1-DFN1006-3	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



Top View

Z5 = Product Type Marking Code
Bar Denotes Gate and Source Side

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current (Note 5) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	1.35	A
		$T_A = +70^\circ\text{C}$		1.03	
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	6	A
Maximum Body Diode continuous Current			I_S	1	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	0.5	W
	$T_A = +70^\circ\text{C}$		0.3	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	278	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	100	nA	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 1	μA	$V_{GS} = \pm 6\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.35	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	170	m Ω	$V_{GS} = 4.5\text{V}, I_D = 1\text{A}$
			—	230		$V_{GS} = 2.5\text{V}, I_D = 1\text{A}$
			—	250		$V_{GS} = 1.8\text{V}, I_D = 1\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	—	1.4	—	S	$V_{DS} = 10\text{V}, I_D = 1\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 150\text{mA}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	94	—	pF	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	12	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	10	—	pF	
Gate resistance	R_g	—	87.1	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	1.4	—	nC	$V_{DS} = 10\text{V}, I_D = 250\text{mA}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	3.1	—	nC	
Gate-Source Charge	Q_{gs}	—	0.13	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.14	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	4.3	—	ns	$V_{DD} = 10\text{V}, V_{GS} = 4.5\text{V}, R_L = 47\Omega, R_G = 10\Omega, I_D = 200\text{mA}$
Turn-On Rise Time	t_r	—	6.1	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	59.4	—	ns	
Turn-Off Fall Time	t_f	—	25.4	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

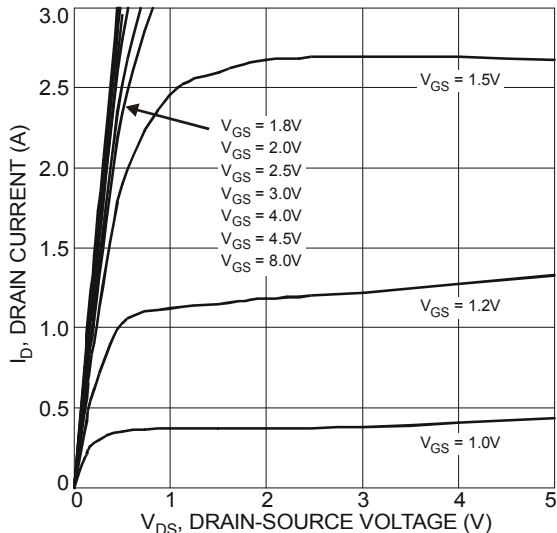


Figure 1 Typical Output Characteristic

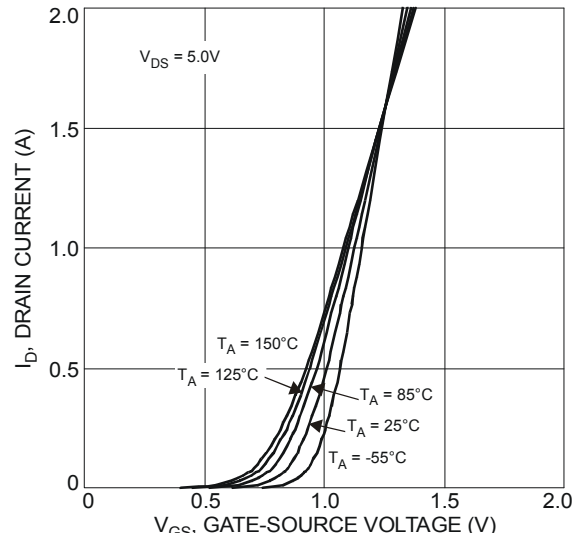


Figure 2 Typical Transfer Characteristics

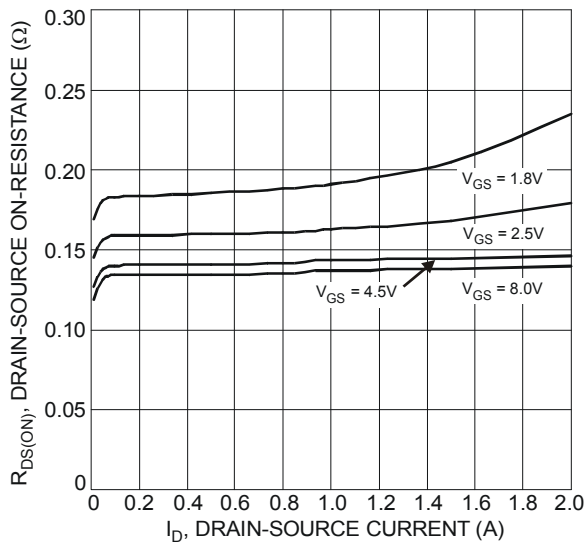


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

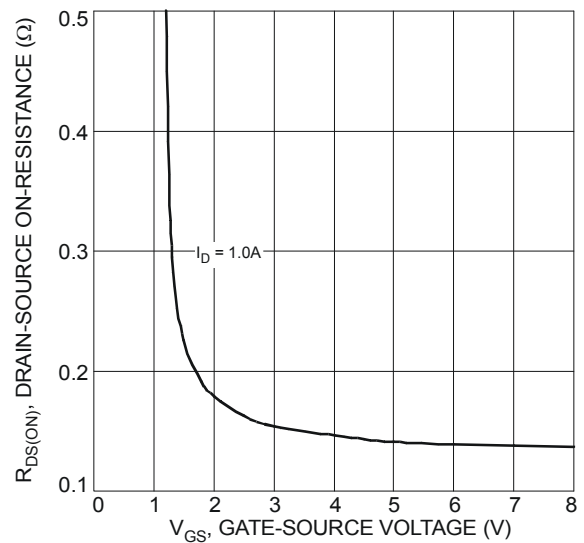


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

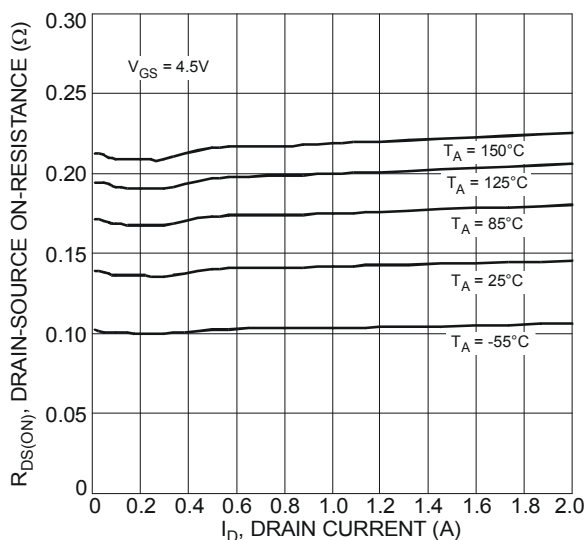


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

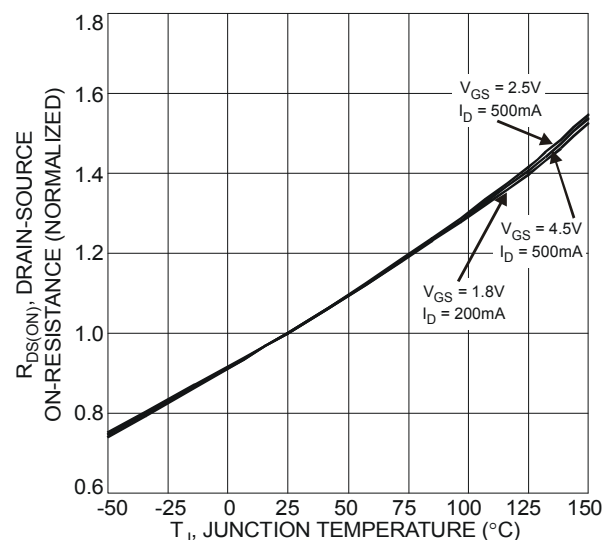


Figure 6 On-Resistance Variation with Temperature

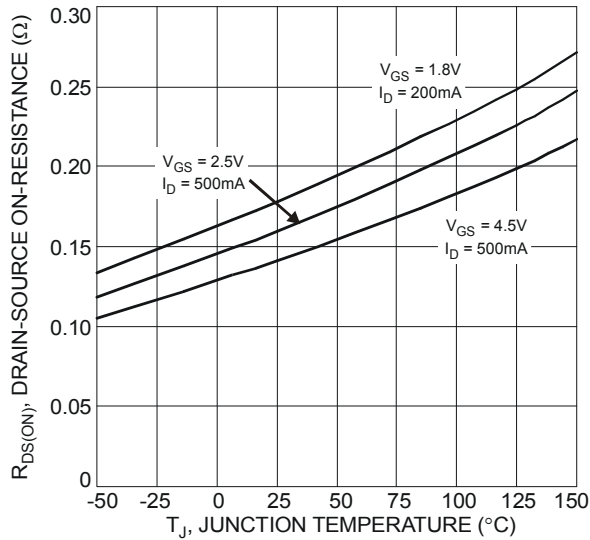


Figure 7 On-Resistance Variation with Temperature

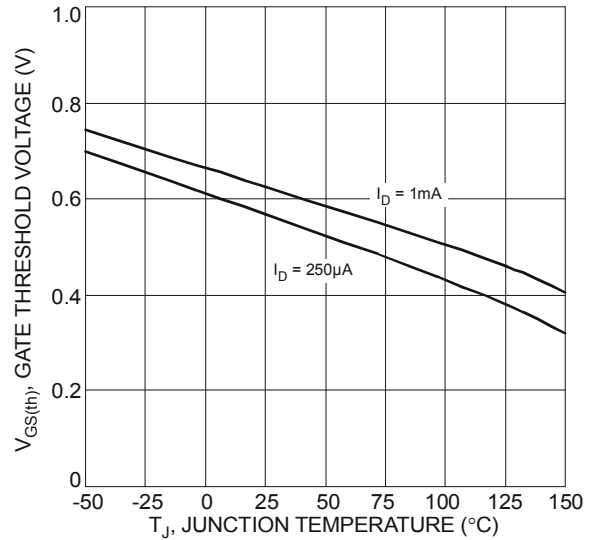


Figure 8 Gate Threshold Variation vs. Ambient Temperature

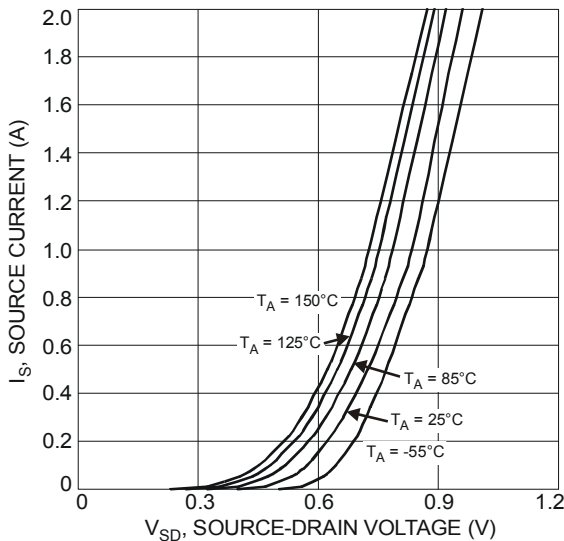


Figure 9 Diode Forward Voltage vs. Current

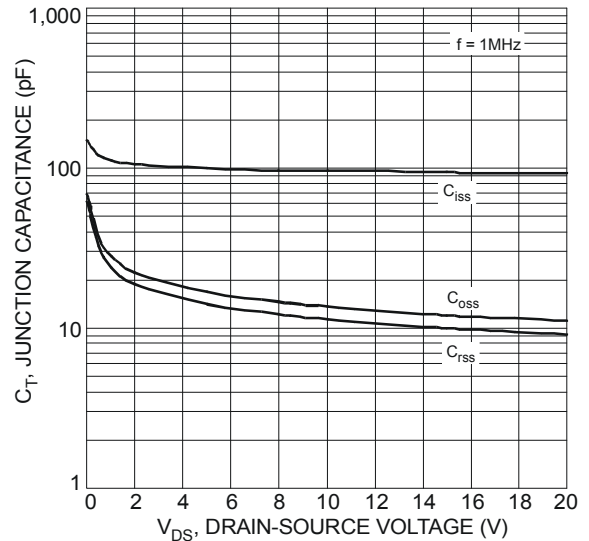


Figure 10 Typical Junction Capacitance

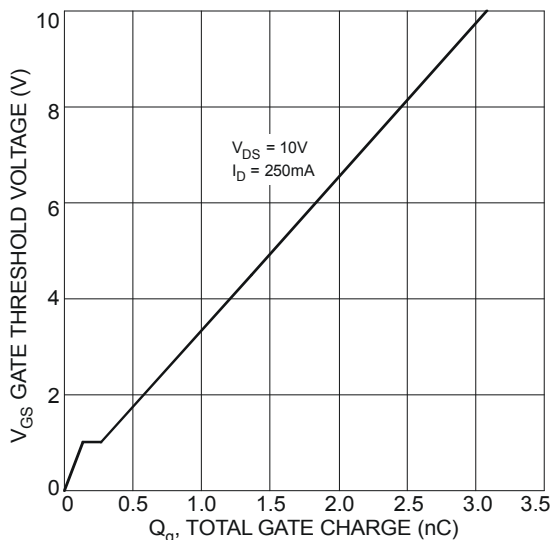
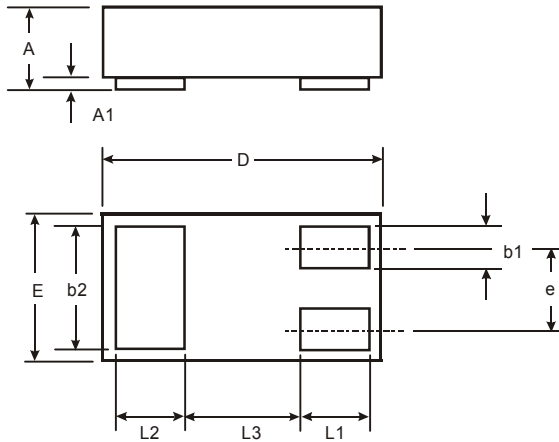


Figure 11 Gate Charge

Package Outline Dimensions

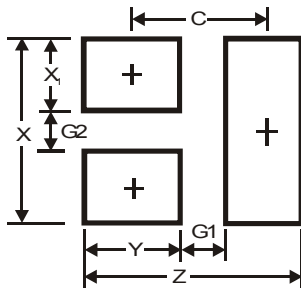
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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